

2SD1739

Silicon PNP Triple-Diffused Planar Type

Horizontal Deflection Output

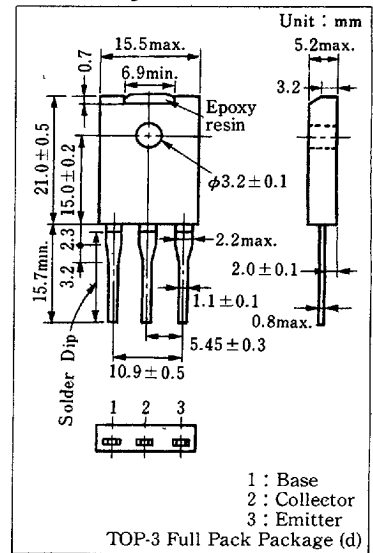
■ Features

- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (T_c=25°C)

Item	Symbol	Value	Unit	
Collector-base voltage	V _{CB0}	1500	V	
Collector-emitter voltage	V _{CES}	1500	V	
	V _{CEO}	700	V	
Emitter-base voltage	V _{EBO}	7	V	
Peak collector current	I _{CP}	18	A	
Collector current	I _C	6	A	
Base current	I _B	2.5	A	
Collector power dissipation	P _C	T _c = 25°C	100	W
		T _a = 25°C	3	
Junction temperature	T _J	150	°C	
Storage temperature	T _{stg}	-55 ~ +150	°C	

■ Package Dimensions



■ Electrical Characteristics (T_c=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CB0}	V _{CB} = 750 V, I _E = 0			10	μA
		V _{CB} = 1500 V, I _E = 0			1	mA
Emitter-base voltage	V _{EBO}	I _E = 1 mA, I _C = 0	7			V
DC current gain	h _{FE}	V _{CE} = 5 V, I _C = 1 A	6		30	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 5 A, I _B = 1.2 A			8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 5 A, I _B = 1.2 A			1.5	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 1 A, f = 0.5 MHz		2		MHz
Storage time (L load)	t _{stg}	I _C = 5 A, I _{B1} = 1.2 A			10	μs
Fall time (L load)	t _f	I _{B2} = -1.2 A, L _B = 5 μH			0.8	μs
Storage time (R load)	t _{stg}	I _C = 5 A, I _{B1} = 1 A		1.5		μs
Fall time (R load)	t _f	I _{B2} = -2 A, V _{CC} = 200 V		0.2		μs

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